L	Hits	Search Text	DB	Time stamp
Number				
1	0	"6649287"	USPAT; US-PGPUB;	2003/11/05 15:55
			EPO; JPO;	15.55
			DERWENT;	
		H0000074FF0H	IBM_TDB	2003/11/05
2	2	"20020074552"	USPAT; US-PGPUB;	16:06
			EPO; JPO;	
			DERWENT;	
3	14	   "763972"	IBM_TDB USPAT;	2003/11/05
3	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	703312	US-PGPUB;	15:56
			EPO; JPO;	
			DERWENT;	
4	0	20020074552.URPN.	IBM_TDB USPAT	2003/11/05
1				16:06
5	0	20020074552.URPN.	USPAT	2003/11/05
6	409	257/190.ccls.	USPAT;	16:06
	105	20,71,0,0010.	US-PGPUB;	16:07
			EPO; JPO;	
			DERWENT;	
7	. 199	257/190.ccls. and (Gallium or AlGaN or	USPAT;	2003/11/05
, ·		GaN)	US-PGPUB;	16:13
			EPO; JPO; DERWENT;	
			IBM TDB	
8	0	((Gallium near3 nitride\$1) or AlGaN or	USPĀT;	2003/11/05
		GaN) with epitaxil	US-PGPUB; EPO; JPO;	16:15
	,		DERWENT;	
	,		IBM_TDB	
9	0	((Gallium near3 nitride\$1) or AlGaN or	USPAT;	2003/11/05
		GaN) with epitax*5	US-PGPUB; EPO; JPO;	16:16
			DERWENT;	
			IBM_TDB	0000/11/05
10	1901	((Gallium near3 nitride\$1) or AlGaN or GaN) with epitax\$5	USPAT; US-PGPUB;	2003/11/05
		Gan) with epitaxy3	EPO; JPO;	10.10
			DERWENT;	
11	27	(((Gallium near3 nitride\$1) or AlGaN or	IBM_TDB USPAT;	2003/11/05
111	"	GaN) with epitax\$5) and ((Gallium near3	US-PGPUB;	16:48
		nitride\$1) or AlGaN or GaN) with	EPO; JPO;	
		((silicon near germanium) or SiGe or "Si.sub.x Ge.sub.1-x")	DERWENT; IBM TDB	
12	14	((Gallium near3 nitride\$1) or AlGaN or	USPAT;	2003/11/05
		GaN) and (((silicon near germanium) or	US-PGPUB;	18:10
		SiGe or "Si.sub.x Ge.sub.1-x") with	EPO; JPO; DERWENT;	
		graded)	IBM TDB	
13	368	((Gallium near3 nitride\$1) or AlGaN or	USPAT;	2003/11/05
		GaN) same (((silicon near germanium) or SiGe or "Si.sub.x Ge.sub.1-x") )	US-PGPUB; EPO; JPO;	17:05
		Side of Si.Sub.x Ge.Sub.i-x")	DERWENT;	
			IBM_TDB	
14	19	1 1 1 =	USPAT;	2003/11/05
		GaN) and (((silicon near germanium) or SiGe or "Si.sub.x Ge.sub.1-x") with	US-PGPUB; EPO; JPO;	17:41
		buffer)	DERWENT;	
			IBM_TDB	2002/31/05
15	0	19802977.URPN.	USPAT	2003/11/05 17:17

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16	2608	((Gallium near3 nitride\$1) or AlGaN or	USPAT;	2003/11/05
		GaN) and (((silicon near germanium) or	US-PGPUB;	17:23
		SiGe or "Si.sub.x Ge.sub.1-x" or silicon	EPO; JPO;	
		or GeSi or Si) near2 substrate )	DERWENT;	
			IBM_TDB	
17	2367		USPAT;	2003/11/05
		GaN) and (((silicon near germanium) or	US-PGPUB;	17:24
		SiGe or "Si.sub.x Ge.sub.1-x" or silicon	EPO; JPO;	
ł		or GeSi or Si) near2 substrate )) and	DERWENT;	
		(((silicon near germanium) or SiGe or	IBM TDB	
		"Si.sub.x Ge.sub.1-x" or silicon or	_	1
		GeSi))		
18	574	<i>-</i> ,	USPAT;	2003/11/05
10	0,1	GaN) and (((silicon near germanium) or	US-PGPUB;	17:25
		SiGe or "Si.sub.x Ge.sub.1-x" or silicon	EPO; JPO;	1,120
		or GeSi or Si) near2 substrate )) and	DERWENT;	
		(((silicon near germanium) or SiGe or	IBM TDB	
		"Si.sub.x Ge.sub.1-x" or silicon or GeSi)	1511_155	
		with buffer)		
1,0	25.6		IICDAM.	2003/11/05
19	356		USPAT;	17:27
		GaN) and (((silicon near germanium) or SiGe or "Si.sub.x Ge.sub.1-x" or silicon	US-PGPUB;	17:27
			EPO; JPO;	
		or GeSi or Si) near2 substrate )) and	DERWENT;	
		(((silicon near germanium) or SiGe or	IBM_TDB	
		"Si.sub.x Ge.sub.1-x" or silicon or GeSi)		
		near3 buffer)	l	
20	22	(((Gallium near3 nitride\$1) or AlGaN or	USPAT;	2003/11/05
		GaN) and (((silicon near germanium) or	US-PGPUB;	17:27
		SiGe or "Si.sub.x Ge.sub.1-x" or silicon	EPO; JPO;	
		or GeSi or Si) near2 substrate )) and	DERWENT;	
		(((silicon near germanium) or SiGe or	IBM_TDB	]
		"Si.sub.x Ge.sub.1-x" or GeSi) near3		
		buffer)		
21	2	"6464780" and GaN	USPAT;	2003/11/05
			US-PGPUB;	17:42
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
26	2	"20030011000"	USPAT;	2003/11/05
			US-PGPUB;	17:50
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
33	6	((Gallium near3 nitride\$1) or AlGaN or	USPĀT;	2003/11/05
-	J	GaN) with (((silicon near germanium) or	US-PGPUB;	18:10
		SiGe or "Si.sub.x Ge.sub.1-x") near2	EPO; JPO;	
		substrate)	DERWENT;	
	:		IBM TDB	<b>{</b>
1		<u> </u>	1	1